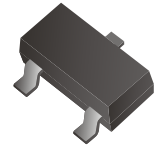


## CDSH3-222N-G/222P-G

**Reverse Voltage: 80 Volts**  
**Power Dissipation: 150 mW**  
**RoHS Device**



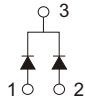
### Features

- Design for mounting on small surface.
- High speed switching.
- High mounting capability, strong surge withstand, high reliability.

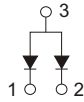
### Mechanical data

- Case: SOT-523, molded plastic.
- Terminals: solderable per MIL-STD-750, method 2026.
- Approx. weight: 0.002 grams

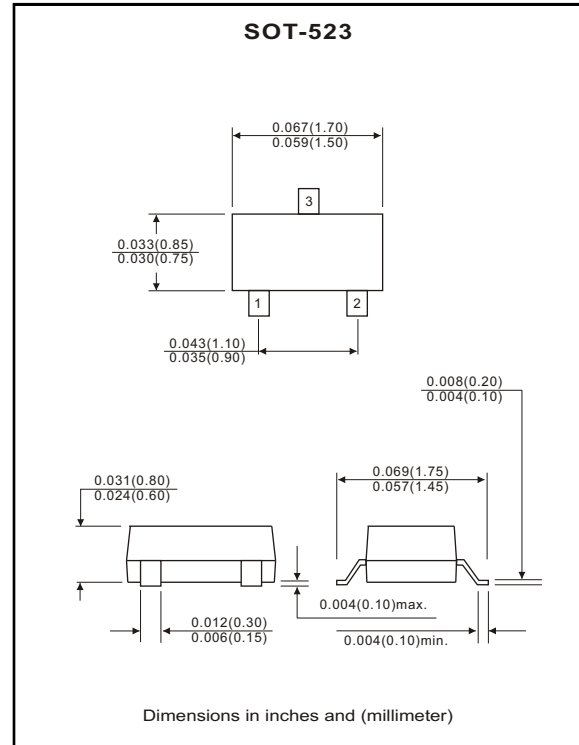
### Circuit diagram



CDSH3-222N-G



CDSH3-222P-G



### Maximum Ratings and Electrical Characteristics

(at Ta=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Value	Units
Repetitive peak reverse voltage	V <sub>RRM</sub>		80	V
Reverse voltage	V <sub>R</sub>		80	V
Peak forward current	I <sub>F</sub>		300	mA
Peak surge forward current	I <sub>FSM</sub>	T=1.0 sec	4	A
Power dissipation	P <sub>D</sub>		150	mW
Maximum forward voltage	V <sub>F</sub>	@I <sub>F</sub> =100mA	1.2	V
Maximum reverse current	I <sub>R</sub>	@V <sub>R</sub> =70V	0.1	μA
Maximum reverse recovery time	T <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =5mA, R <sub>L</sub> =100Ω	4	nS
Maximum diode capacitance	C <sub>J</sub>	V <sub>R</sub> =6V, f=1.0MHz	3.5	pF
Maximum junction temperature	T <sub>J</sub>		150	°C
Storage temperature	T <sub>STG</sub>		-55 to +150	°C

## RATING AND CHARACTERISTIC CURVES (CDSH3-222N-G/222P-G)

Fig.1 Forward Characteristics (P type)

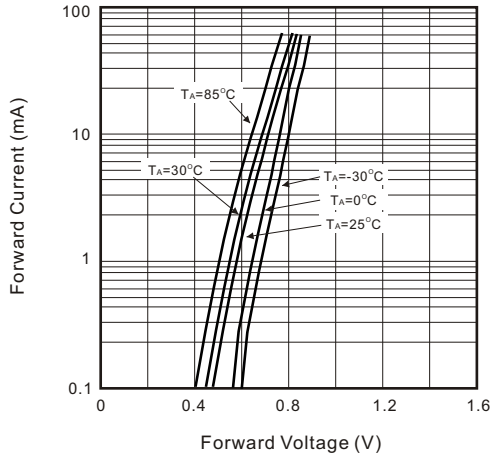


Fig.2 Reverse Characteristics (P type)

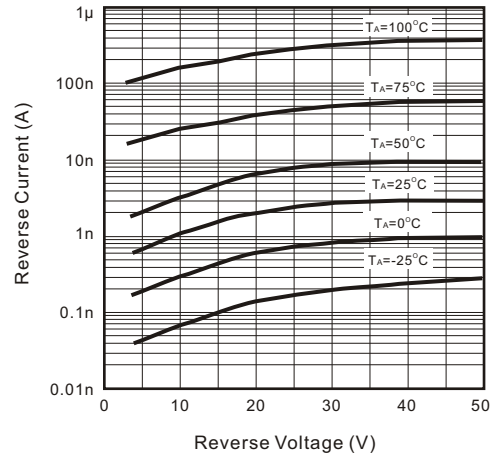


Fig.3 Forward Characteristics (N type)

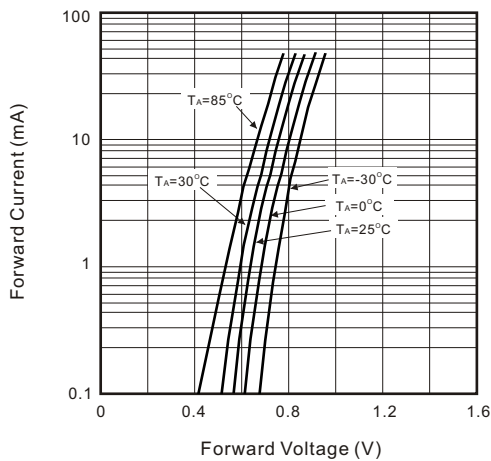


Fig.4 Reverse Characteristics (N type)

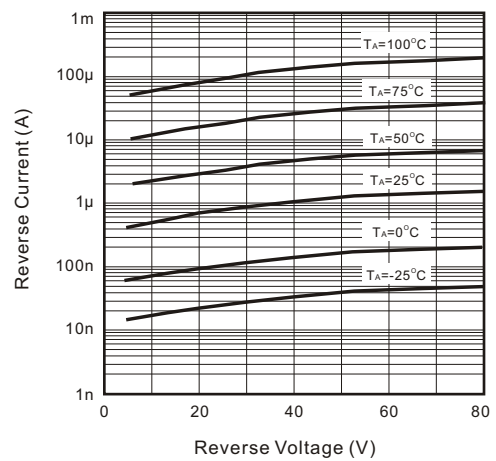


Fig.5 Capacitance Between Terminals Characteristics

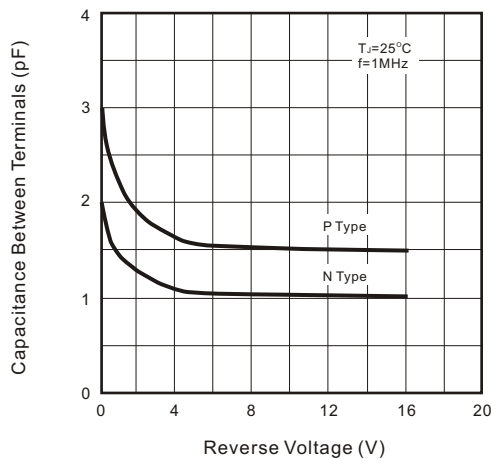


Fig.4 Power Derating Curve

